	L#	Hits	Search Text	DBs	Time Stamp
	<del>                                     </del>	2504	(Si?sub.\$3 near1 Ge?sub.\$3) (SiGe	USPAT; US-PGPUB; EPO;	2002/01/30
1  L	L5	3564	GeSi)	JPO; DERWENT; IBM_TDB	16:51
2	1		strained adj2 (Si silicon)	USPAT; US-PGPUB; EPO;	2002/01/30
	L12			JPO; DERWENT; IBM_TDB	17:08
3	L19	0	strained adj2 (Si/)	USPAT; US-PGPUB; EPO;	2002/01/30
				JPO; DERWENT; IBM_TDB	
4	1.06	11	strained adj2 Si/SiGe	USPAT; US-PGPUB; EPO;	2002/01/30
	L26			JPO; DERWENT; IBM_TDB	
_	1	71	5 and 12	USPAT; US-PGPUB; EPO;	2002/01/30
5	L33			JPO; DERWENT; IBM_TDB	17:12
	***************************************	······································	33 and (thick thickness nm	USPAT; US-PGPUB; EPO;	2002/01/30
6	L40	65	nanometer ang angstrom	JPO; DERWENT; IBM_TDB	17:14
			micrometer ".mu.m")		
			5 same (thick thickness nm	USPAT; US-PGPUB; EPO;	2002/01/30
7	L47	1010	nanometer ang angstrom	JPO; DERWENT; IBM_TDB	17:15
			micrometer ".mu.m")	USPAT; US-PGPUB; EPO;	2002/01/30
8	L54	54	12 and 47	JPO; DERWENT; IBM_TDB	19:00
Ľ				USPAT; US-PGPUB; EPO;	
9	L61	3	5906951.pn.	JPO; DERWENT; IBM_TDB	18:35
			·	LIEDAT: US POPI IR: FPO:	2002/01/30
10	L68	77854	bond\$3 near15 (temperature degree	JPO; DERWENT; IBM_TDB	19:17
<u>                                     </u>			".degree.C")	USPAT; US-PGPUB; EPO;	
11	L75	179	5 and 68	JPO; DERWENT; IBM_TDB	
Ľ.		<b></b>	68 same (nitrogen or "N.sub.2" or ai	LISPAT: US-PGPUB: FPO:	2002/01/30
12	L82	6298	68 same (nitrogen of 14.sub.2 of all	JPO; DERWENT; IBM_TDB	19:18
<u> </u>	4		or argon or Ar)	USPAT; US-PGPUB; EPO;	
13	L89	15	5 and 82	JPO; DERWENT; IBM_TDE	19:04
L.			L JAC (Assessment Los dosses)	USPAT; US-PGPUB; EPO;	
14	L96	179693	bond\$3 same (temperature degree ".degree.C")	JPO; DERWENT; IBM_TDE	
<u> </u>			96 same (nitrogen or "N.sub.2" or ai	USPAT: US-PGPUB: FPO:	2002/01/30
15	L103	20589	or argon or Ar)	JPO; DERWENT; IBM_TDE	19:18
<u> </u>	<b>-</b>			USPAT; US-PGPUB; EPO;	2002/01/30
16	L110	48	5 and 103	JPO; DERWENT; IBM_TDE	19:19
1.					

	L#	Hits	Search Text	DBs	Time Stamp	
	1. 4	205	447/07	USPAT; US-PGPUB; EPO;	2002/01/30	
1	L1	285	117/97.ccls.	JPO; DERWENT; IBM_TDB	12:29	
_	1		(Si?sub.\$3 near1 Ge?sub.\$3) (SiGe	USPAT; US-PGPUB; EPO;	2002/01/30	
2	L8	3564	GeSi)	JPO; DERWENT; IBM_TDB	12:29	
	1			USPAT; US-PGPUB; EPO;	2002/01/30	
3	L15	13210	silicon near1 germanium	JPO; DERWENT; IBM_TDB		
	<b>-</b>			USPAT; US-PGPUB; EPO;	2002/01/30	
4	L22	14	1 and 8	JPO; DERWENT; IBM_TDB		
				USPAT: US-PGPUB; EPO;	<u> </u>	
5	L29	33	1 and 15	JPO; DERWENT; IBM_TDB		
	<del> </del>			USPAT; US-PGPUB; EPO;	<b>4</b>	
6	L36	23	29 not 8	JPO; DERWENT; IBM_TDB		
	-		((chemo chem chemical) near1	USPAT; US-PGPUB; EPO;	<b></b>	
7	L43	14438	(mech mechanical)) near2 polish\$3	JPO; DERWENT; IBM_TDB		
				USPAT; US-PGPUB; EPO;	•	
8	L50	15461	cmp	JPO; DERWENT; IBM_TDB		
<u> </u>	-			USPAT; US-PGPUB; EPO;	<b>4</b> **** **** **** **** **** **** *** ***	
9	L57	21517	43 50	JPO; DERWENT; IBM_TDB		
<u> </u>	<b>-</b>	ļ		USPAT; US-PGPUB; EPO;	å	
10	L64	622	57 and (8 15)	JPO; DERWENT; IBM_TDB		
ļ	<b></b>			USPAT: US-PGPUB; EPO;	<b>•</b>	
11	L71	129	64 and (bonded bonding)	JPO; DERWENT; IBM_TDB		
	<b>-</b>	·	04 1 (// 1 - 1 h 1 - 2)	USPAT; US-PGPUB; EPO;	<b>•</b>	
12	L78	95	64 and ((bonded bonding) near15	JPO; DERWENT; IBM_TDB		
<u> </u>			(wafer substrate))	±	<b>4</b>	
13	L85	492	57 same (bonded bonding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		
				A	<b>•</b>	
14	L92	165	57 near20 (bonded bonding)	USPAT; US-PGPUB; EPO;		
Ľ.	<b>_</b>			JPO; DERWENT; IBM_TDB		
15	L99	153	92 and (silicon or semiconductor)	USPAT; US-PGPUB; EPO;		
<u> </u>				JPO; DERWENT; IBM_TDB		
16	L106	5	43 near20 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB		
<u> </u>						
17	L113	6861	43 near20 (si substrate wafer	USPAT; US-PGPUB; EPO;		
Ľ.,			semiconductor silicon)	JPO; DERWENT; IBM_TDB	<b>A</b>	
18	L120	62	113 same (RMS or roughness)	USPAT; US-PGPUB; EPO;		
L.				JPO; DERWENT; IBM_TDB	<b>4</b>	
19	L127	17	120 and (bonded bonding)	USPAT; US-PGPUB; EPO;		
				JPO; DERWENT; IBM_TDB	<b>*</b> * * * * * * * * * * * * * * * * * *	
20	L134	92	(si substrate wafer semiconductor	USPAT; US-PGPUB; EPO;	2002/01/30	
20			silicon) same rms same bond\$3	JPO; DERWENT; IBM_TDB		
21	L141	9	43 and 134	USPAT; US-PGPUB; EPO;	2002/01/30	
<u></u>				JPO; DERWENT; IBM_TDB		
22	L148	0	2001WO-US19613.ap,prai.	USPAT; US-PGPUB; EPO;	2002/01/30	
			200 ; ¥¥0=00 ; 00 ; 10. ap,p; ai.	JPO; DERWENT; IBM_TDB	<b></b>	
22	L155	0	2001WO-US19613	USPAT; US-PGPUB; EPO;		
23				JPO; DERWENT; IBM_TDB	å	
24	1.162	Λ	2001WO-US99169	USPAT; US-PGPUB; EPO;		
24	L162	٧	200100-0333103	JPO; DERWENT; IBM_TDB	15:36	

	L#	Hits	Search Text	DBs	Time Stamp
1	L1	3564	(Si?sub.\$3 near1 Ge?sub.\$3) (SiGe GeSi)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/01/30 11:10
2	L8	41	1 and (graded or gradient) and relaxed and bond\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	L15	6	1 and (stepped) and relaxed and bond\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	